

CLAIMS

What is claimed is:

- 1 1. An apparatus, comprising:
2 a first memory cell coupled to a first bit line;
3 a second memory cell coupled to a second bit line;
4 an address decoder coupled to the first and second memory cells to
5 enable access to the first and second memory cells; and
6 a comparator circuit coupled to the first and second bit lines to compare
7 the voltage level on the first bit line with the voltage level on the second bit at a
8 time when data is output from the first memory cell on the first bit line and
9 from the second memory cell on the second bit line.
- 1 2. The apparatus of claim 1, wherein the address decoder decodes
2 part of a memory address.
- 1 3. The apparatus of claim 1, wherein the first and second memory
2 cells are dynamic RAM memory cells.
- 1 4. The apparatus of claim 1, wherein the first and second memory
2 cells are static RAM memory cells.
- 1 5. The apparatus of claim 1, wherein the comparator circuit is
2 comprised of a single comparator with a first input coupled to the first bit line
3 and a second input coupled to the second bit line.

1 16. The method of claim 14, further comprising setting the degree to
2 which the difference in voltage levels between the first bit line and the second
3 bit line is substantial.

1 17. A comparator circuit in a memory array comprising:
2 a first input coupled to a first bit line that is coupled to a first memory
3 cell in the memory array;
4 a second input coupled to a second bit line that is coupled to a second
5 memory cell in the memory array; and
6 an output coupled to a sticky latch.

1 18. The comparator circuit of claim 17, wherein the comparator circuit
2 is coupled to a multiplexer to disconnect the second bit line, and to connect a
3 third bit line that is coupled the first memory cell in the memory array.